150 V, 1 A PNP high-voltage low VCEsat transistor

22 March 2022

Product data sheet

1. General description

PNP high-voltage low V_{CEsat} transistor in a SOT23 (TO-263AB) small Surface-Mounted Device (SMD) plastic package. NPN complement PBHV8115T-Q.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_{C} and I_{CM}
- High collector current gain (hFE) at high IC
- Small SMD plastic package
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- · LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-150	V
Ic	collector current		-	-	-1	Α
h _{FE}	DC current gain	V_{CE} = -10 V; I_{C} = -50 mA; T_{amb} = 25 °C	100	220	-	



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5. Pinning information

Table 2. Pinning information

Symbol	Description	Simplified outline	Graphic symbol
В	base	3	С
Е	emitter		j
С	collector		В
			 E
		1	sym013
	B E	B base E emitter	B base E emitter C collector

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PBHV9115T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV9115T-Q	W7%

[1] % = placeholder for manufacturing site code

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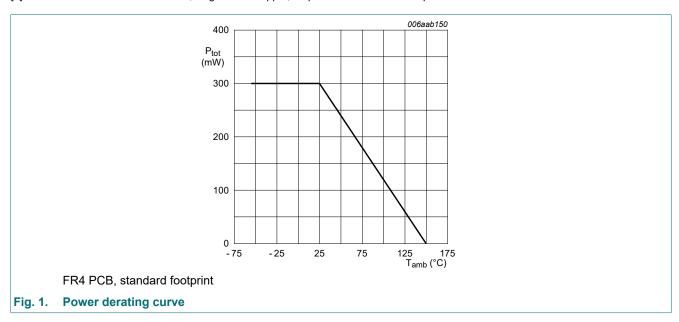
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-200	V
V_{CEO}	collector-emitter voltage	open base		-	-150	V
V_{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-2	Α
I _{BM}	peak base current			-	-400	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



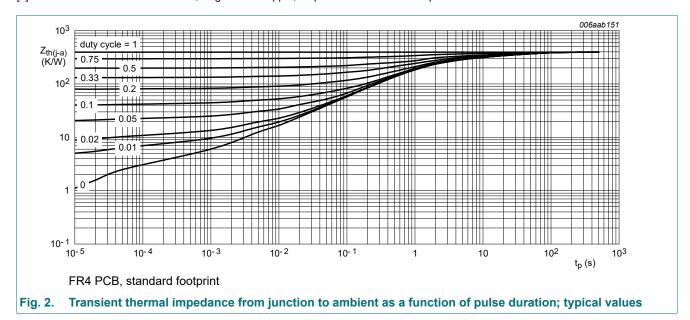
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



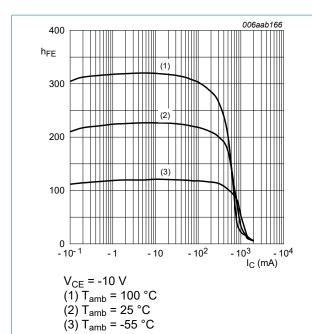
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -120 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -120 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -120 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -10 V; I _C = -50 mA; T _{amb} = 25 °C	100	220	-	
		V _{CE} = -10 V; I _C = -100 mA; T _{amb} = 25 °C	100	220	-	
		V_{CE} = -10 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	10	30	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -100 mA; I _B = -10 mA; T _{amb} = 25 °C	-	-60	-120	mV
		I _C = -100 mA; I _B = -20 mA; T _{amb} = 25 °C	-	-50	-100	mV
		I_C = -500 mA; I_B = -100 mA; T_{amb} = 25 °C	-	-150	-300	mV
V _{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -200 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-1.05	-1.2	V
t _d	delay time	$V_{CC} = -6 \text{ V}; I_C = -0.5 \text{ A}; I_{Bon} = -0.1 \text{ A};$	-	8	-	ns
t _r	rise time	I _{Boff} = 0.1 A; T _{amb} = 25 °C	-	282	-	ns
t _{on}	turn-on time		-	290	-	ns
t _s	storage time		-	430	-	ns
t _f	fall time		-	300	-	ns
t _{off}	turn-off time		-	730	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	-	115	-	MHz
C _c	collector capacitance	V _{CB} = -20 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	10	-	pF
C _e	emitter capacitance	V _{EB} = -0.5 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	150	-	pF

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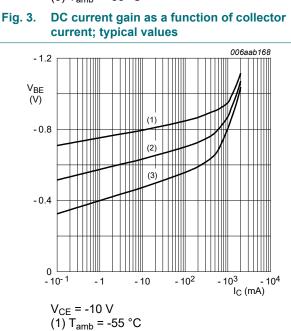


Fig. 5. Base-emitter voltage as a function of collector current; typical values

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) T_{amb} = 100 °C

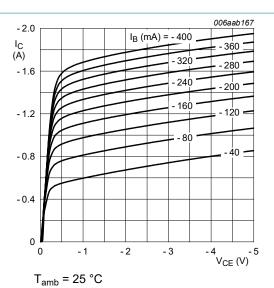
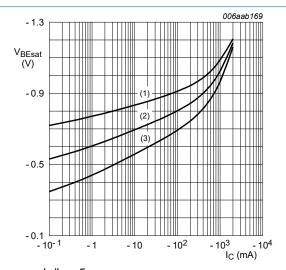


Fig. 4. Collector current as a function of collectoremitter voltage; typical values



 $I_{C}/I_{B} = 5$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

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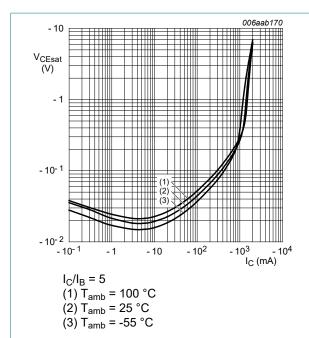


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

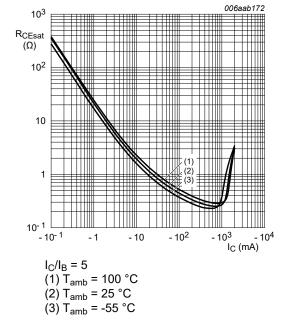


Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values

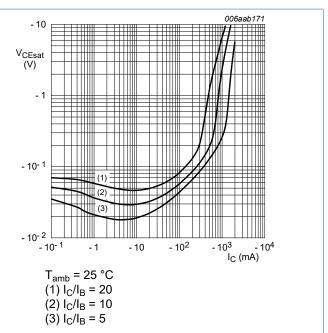


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

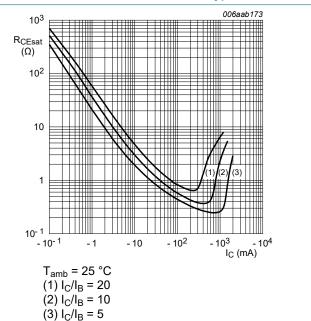
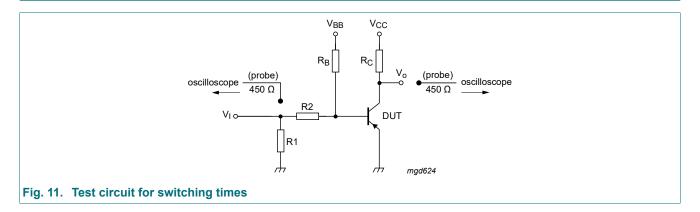


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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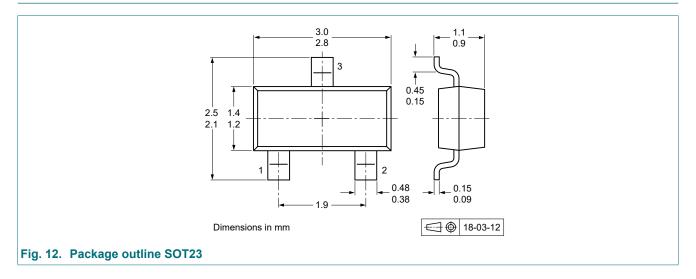
11. Test information



Quality information

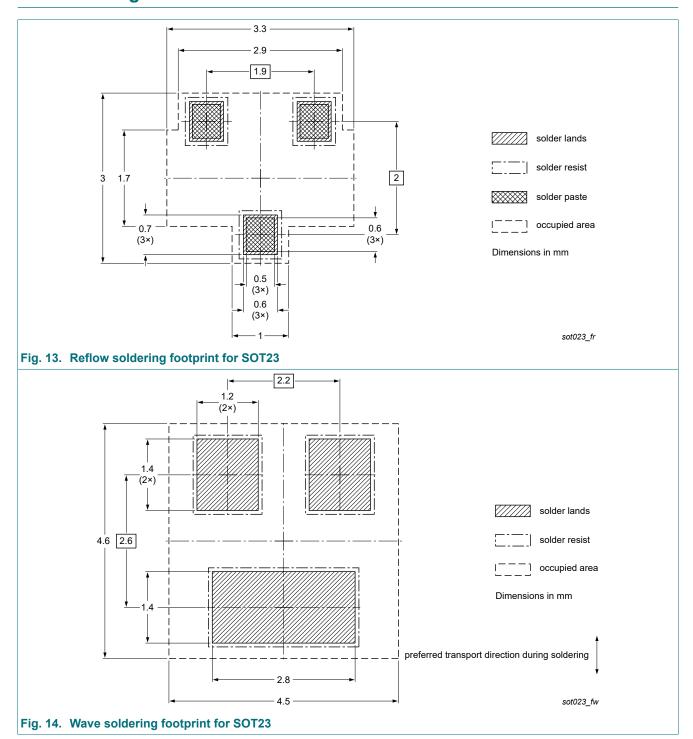
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9115T-Q v.1	20220322	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 22 March 2022

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